

### INDIAN INSTITUTE OF INFORMATION TECHNOLOGY UNA HIMACHAL PRADESH

An Institute of National Importance under MoE

Saloh, Una - 177 209

Website: www.iiitu.ac.in

### AY 2023-24

#### **School of Electronics**

### **CURRICULUM: IIITUGECE22**

#### **END SEMESTER EXAMINATION**

26 Dec.' 2023 (9:00 - 12:00 hrs)

Degree		25 (7.00 – 12.00	mis)
Degree	B. Tech.	Branch	ECE
Semester	III		
Subject Code & Name	ECC301: Ele	ctronic Devices a	nd Circuits
Time: 180 Minutes	Answer	All Questions	Maximum: 100 Marks

S. No.	Question	Marks
1 <sub>a</sub>	State advantages and disadvantages of PN and Zener diode. Explain the working principle and construction of Zener diode in detail.	5
1.b	Explain the input and output characteristics of NPN transistor in CB configuration with transistor hybrid parameter models	5
1.c	Draw the basic construction of a P-channel JFET. Apply the proper biasing between the drain and source and sketch the depletion region for $V_{ca} = 0V$	5
1.d	by temperature parameters. Also, show diagrammatically the variation in diode characteristics with temperature variation	5
2,2	A transistor operating in CB configuration has $I_C$ =2.98 mA, $I_E$ =3.2 mA, and $I_{CO}$ =0.02 mA. What current will flow in the collector circuit of this transistor when connected in CE configuration with $I_{R}$ =30 $\mu$ A?	5
•	Determine the dc bias voltage $V_{CE}$ and the current $I_C$ for the voltage divider configuration of Figure 1.	5
	Figure 1	

Titifoda Bansal



### INDIAN INSTITUTE OF INFORMATION TECHNOLOGY UNA (HP)

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#### AY 2022-23

School of Electronics

**CURRICULUM: HITUGECE22** 

Cycle Test – II 28, Oct.'22

Time: 9:00AM-10:00AM

Time: 60 Minutes	Answer	All Questions	Maximum: 20 Marks
Subject Code & Name	ECC301: Ele	ctronic Devices ar	nd Circuits
Semester	Ш		
Degree	B. Tech.	Branch	ECE

SI. No.	Question	Marks
1.a	State advantages and disadvantages of a photodiode and LED Diode.	(1)
7.6	Define Tunnel diode? Explain the operation of Tunnel diode with its equivalent circuit and mention its applications.	(2)
1.6	What is rectification? Explain the working of bridge full-wave rectifier with relevant circuit diagram and waveforms.	(2)
2.8	What is requirement of voltage multiplier? Also, draw the circuit diagram of voltage doubler.	(1)
2.b	In the Fig. 1, assume that the diodes $D_1$ and $D_2$ are ideal. Obtain the average value of voltage Vab (in volts) across terminals 'a' and 'b'.	(2)
2.c	Two silicon diodes, with a forward voltage drop of 0.7 V, are used in the circuit shown in the Fig 2. Obtain the range of input voltage $V_i$ for which the output voltage $V_0 = V_i$ .  Fig. 2	(2)

3.a	What is Early effect? Explain how it affects the BJT characteristics in CB	(1
3.b	configuration.  A NPN BJT having reverse saturation current $I_S = 10^{-15}$ A is biased in the forward active region with $V_{BE} = 700$ mV and the current gain ( $\beta$ ) may vary from 50 to 150 due to manufacturing variations. Determine the maximum emitter current (in $\mu$ A) of	(2)
	BJT.  Explain input and output characteristics of NPN transistor in CB configuration with	(2)
3.6	near diagram.	
4.a	reverse bias saturation current $I_{CO}$ is 0.0 $\mu$ M. The emitter mode and operated in the active region with a base drive current $I_B = 20 \mu$ M.	(1)
	Calculate the collector current I <sub>C</sub> for this mode of operation.  Draw the circuit diagram of a voltage divider bias and derive expression for Stability	(2)
4.b	factor.	
	Fig. 3 shows biasing with base resistor method. (i) Determine the collector current $I_C$ and collector-emitter voltage $V_{CE}$ for $\beta = 50$ . (ii) If $R_B$ in this circuit is changed to 50 k $\Omega$ , find the new operating point. (Neglect small base-emitter voltage)	
4.c	$\begin{cases} z_{g} = 100 \text{ in} \\ \downarrow z_{g} \end{cases}$ $\begin{cases} z_{e} = 1 \text{ in} \\ \downarrow z_{e} \end{cases}$	(2)
	$\frac{1}{v_{M}=2 V} = \frac{1}{v_{CC}} = 9 V$	
	Fig. 3	

\*\*\*\* GOOD LUCK \*\*\*\*\*



## INDIAN INSTITUTE OF INFORMATION TECHNOLOGY UNA (HP)

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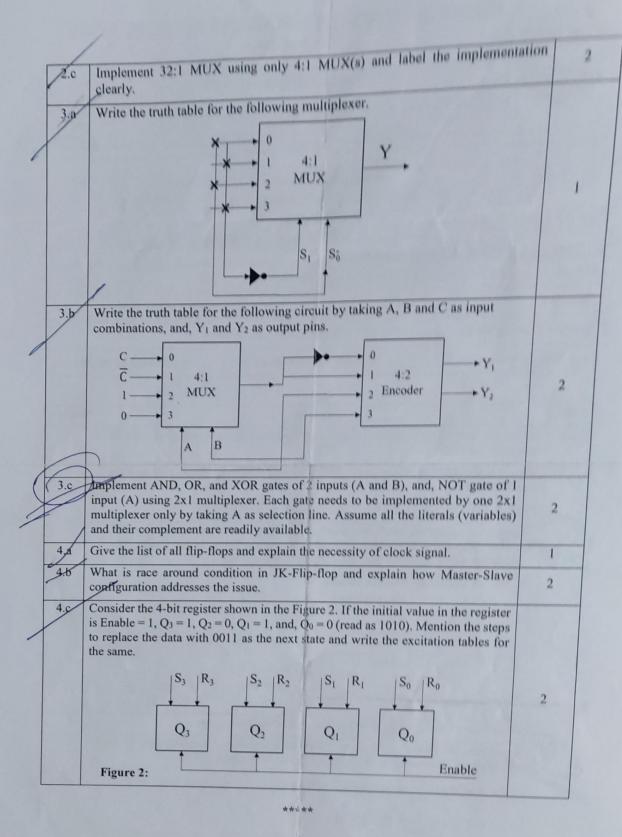
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### School of Electronics CURRICULUM: HITUGECE22

Cycle Test - II November 28, 2022, 02:00 PM-03:00 PM

Degree	B. Tech.	Branch	ECE
Semester	Ш		
Subject Code & Name	ECC302: Digita	l Circuits and S	ystems
Time: 60 Minutes	Answer A	Il Questions	Maximum: 20 Marks

S. No.			Questi	on		Marks	
la	Define the terms Combinational circuit and Sequential Circuit, and give suitable examples for each.						
1.6	Minimize the following function (F <sub>1</sub> ) using suitable K-map and list out all the EPIs and NEPIs if any. $F_1(A, B, C, D) = \sum m (1,2,3,4,5,9,10,12,13,14) + \sum d (0,6,11)$						
(de)	numbers	as inputs and		ut as per the T	that can accept two 2-bit able. In this Figure, Pin-		
	S. No.	Condition	Output value in Hexadecimal	A1	0		
	1.	A=B	(02)16	A <sub>0</sub>	2	2	
	2.	A <b< td=""><td>(04)16</td><td></td><td>Black 3</td><td></td></b<>	(04)16		Black 3		
	3.	A <b< td=""><td>(10)16</td><td>B<sub>1</sub></td><td>box 4</td><td></td></b<>	(10)16	B <sub>1</sub>	box 4		
			Figure 1	В <sub>0</sub> ———	6 7		
2.a	Implem	ent Full adde	r circuit using Half a	dders and basi	c gates.	1	
(2)			ving functions of 'n' ing 'B' as input for F		ng the multiplexer of '(n- nput for F <sub>3</sub> .		
	$F_2(A, B)$	$(C,D) = \sum$	m (1,2,3,4,6,9,12,13	3,14)		2	
1			m (0,2,5,9,11,14,15				





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### School of Electronics CURRICULUM: HITUGECE22

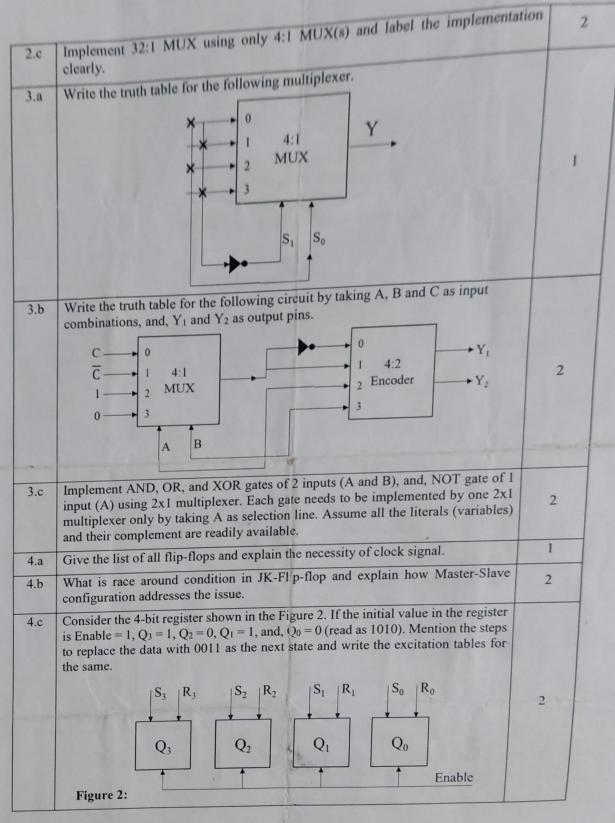
Cycle Test - II

November 28, 2022, 02:00 PM-03:00 PM

Degree	B. Tech.	Branch	ECE
Semester	III		
Subject Code & Name	ECC302: Digital	Circuits and S	ystems
Time: 60 Minutes	Answer All		Maximum: 20 Marks

S. No.			Quest	ion		Marks	
1.a	Define the examples	Define the terms Combinational circuit and Sequential Circuit, and give suitable examples for each.					
1.b	Minimize the following function (F <sub>1</sub> ) using suitable K-map and list out all the EPIs and NEPIs if any. $F_1(A, B, C, D) = \sum m (1,2,3,4,5,9,10,12,13,14) + \sum d (0,6,11)$						
1.c	Design a circuit for the black box provided in Figure 1, that can accept two 2-bit numbers as inputs and provides 8-bit output as per the Table. In this Figure, Pin-7 is considered as the MSB and pin 0 is considered as LSB.						
	S. No.	Condition	Output value in Hexadecimal	A <sub>1</sub>	0		
	1.	A=B	(02)16	A <sub>0</sub>	1 2	2	
	2.	A <b< td=""><td>(04)16</td><td></td><td>Black 3</td><td></td></b<>	(04)16		Black 3		
	3.	A <b< td=""><td>(10)16</td><td>B<sub>1</sub> box 4</td><td></td></b<>	(10)16	B <sub>1</sub> box 4			
			Figure 1:	B <sub>0</sub>	5 6 7		
2.a			circuit using Half a			1	
2.b	$F_2(A, B)$	$(C,D) = \sum_{i=1}^{n} C_{i}$	ving functions of 'n' ng 'B' as input for F $m$ (1,2,3,4,6,9,12,13) $m$ (0,2,5,9,11,14,15)	2 and 'C' as in 3,14)	ng the multiplexer of '(n- put for F <sub>3</sub> .	2	







### UNA [HP]

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### AY 2022-23 School of Electronics Cycle Test – II 29, November '22

Degree			
	B. Tech.	Branch	ECE
Semester	III		DOL
Subject Code & Name	ECC303: Electro	omnometic Fill	11 m
Time: 60 Minutes			ld Theory
oo minutes	Answer All Qu	estions	Maximum: 20 Marks

No.	Question	
	Write True/False:	Marks
1.2	i) Time-varying electric field produces magnetic field. ii) Time-varying magnetic field produces electric field. The parallel-plate transmission V	(1)
1.b	The parallel-plate transmission line shown in the figure 1, with b=4cm and d=8mm, while the medium between the plates is characterized by $\mu_r = 1$ , $\epsilon_r = 1$ , and $\sigma = 0$ . Neglect fields outside the dielectric. Given the field $H = 5Cos(10^9t - \beta z)\vec{y}$ A/m. Use Maxwell's equation to help find $\beta$ , if $\beta > 0$	(2)
	Figure 1: Parallel-Plate Capacitors for Question 1b.  Considering the statement of Question 1(b); Find	
1.c	(i) displacement current density at z=0. (ii) total displacement crossing current the surface at $x = 0.5d$ ; $0 < y < b$ ; $0 < z < 0.1m$ in the $\vec{x}$ direction.	(2)
2.8	Write the four boundary conditions regrading electric and magnetic field at any surface of discontinuity.	(1)
2.1	The phasor electric field expression is given by: $\vec{E} = \left[a_x + \overrightarrow{E_y}a_y + (2+5j)a_z\right]e^{-j2.3(-0.6x+0.8y)}.$ Find the following:	(2)

t 261 550

	a)E <sub>y</sub>	
	b) Francisco and annual month of wave	-
2.0	Determine the current density function associated with the magnetic field given as $\vec{H} = 2\rho \vec{a_0} + 3\vec{a_0} + \cos\theta \vec{a_0}$	(2)
3.a	If electric field of plane wave is: $\vec{E}(z,t) = 3\cos(wt - kz + 30^{\circ})\hat{x} - 3\sin(wt - kz + 45^{\circ})\hat{y}$ (mV/m). The polarization state of plane wave is	(1)
3.b	Derive the expression for parallel and perpendicular polarization of an electromagnetic wave reflected by a Perfect Dielectric for the case of normal incidence.	(2)
3.c	The space-time dependence of electric field of a linearly polarized light in free space is given as $\vec{E} = E_o Cos(\omega t - \beta z) \mathcal{X}$ . Compute the value of the time average energy density associated with the electric field.	(2)
*te	Explain depth of penetration. What will the expression be for a case of good conductor.	(1)
4.b	Two infinitely extended homogeneous isotopic dielectric media (medium-1 and medium-2 with dielectric constant 2 and 5, respectively) meet at the $z=0$ plane as shown in the figure 2. A uniform electric field exists everywhere. For $z \ge 0$ , the electric field is given by $\vec{E} = 2\hat{\imath} - 3\hat{\jmath} + 5\hat{k}$ . The interface separating the two media is charge free. Compute the value of electric displacement vector in the medium-2.	
7.0		(2)
	medium - 1	
	medium - 2 z=0	
	Figure 2: Parallel-Plate Capacitors for Question 4b.	
4.c	Derive the expression for Brewster angle and Critical angle. What is the	2)

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# INDIAN INSTITUTE OF INFORMATION TECHNOLOGY UNA [HP]

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AY 2022-23
School of Electronics
CURRICULUM: IIITUGECE22

Cycle Test – II 29, Nov.'22

Time: 02:00PM-03:00PM

Time: 60 Minutes	Answer All (	Questions	Maximum: 20 Mark	
Subject Code & Name	ECC304: CO	ECC304: COMMUNICATION SYSTEMS		
Semester	Ш			
Degree	B. Tech.	Branch	ECE	

Sl. No.	Question	
1.8	Explain under sampling, over sampling and critical sampling process.	
1.b	An angle modulated signal is given by $S(t) = 10\cos[2\pi 10^6 t + 20\sin 250t + 30\sin 250t]$ . Find Maximum Frequency deviation and Maximum Phase deviation.	2
1.6	A receiver is tuned to 1MHz station. Intermediate frequency (I.F.) is 455KHz and Quality factor is 80. (i) Find Image Rejection Ratio. (ii) Find Image rejection ratio if receiver is tuned to 15 MHz.	2
2.a 2.b	Draw the block diagram of Super-heterodyne receiver for FM.	1
100	Find the Nyquist rate for the following signals:  (i) sinc 100t * sinc 200t (ii) sinc 200t. sinc 300t	2
2.c	Discuss the Direct method for generation of Frequency Modulation in detail.	2
39	Why amplitude limiter cannot be used in case of Amplitude modulation?  Justify it.	1
3.6	Draw block diagram of Pulse Code Modulation scheme and explain each of the block.	2
30	A message signal $10\cos 2\pi 10^4 t$ is transmitted using PCM. Each sample is encoded with 8 bits. Find all possible parameters of PCM.	2
4.8	What is the need of Pre-emphasis and De-emphasis used in Analog Communication.	1
4.b	Explain the working of Tuned Radio Frequency receiver for AM.	2
4.6	A message signal is transmitted by using PCM such that maximum quantization error should be atmost of 1% of peak to peak amplitude of message signal. Find the minimum number of bits per sample required.	2

\*\*\*\* GOOD LUCK \*\*\*\*\*